

Materials List for:

Nanofabrication of Gate-defined GaAs/AlGaAs Lateral Quantum Dots

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Materials

Name	Company	Catalog Number	Comments
Acetone - CH ₃ COCH ₃	Anachemia	AC-0150	67-64-1
Isopropyl Alcohol (IPA) - (CH ₃) ₂ CHOH	Anachemia	AC-7830	67-63-0
1165 Remover	MicroChem Corp	G050200	872-50-4
Microposit MF-319 Developer	ShiPLEY	38460	75-59-2
Sulfuric Acid - H ₂ SO ₄	Anachemia	AC-8750	766-93-9
Hydrogen Peroxide (30%) - H ₂ O ₂	Fisher Scientific		7722-84-1
LOR 5A Lift-off resist	MicroChem Corp	G516608	120-92-3
Microposit S1813 Photo Resist	ShiPLEY	41280	108-65-6
Microposit S1818 Photo Resist	ShiPLEY	41340	108-65-6
PMMA LMW 4% in anisole	MicroChem Corp		100-66-3, 9011-14-7
PMMA HMW 2% in anisole	MicroChem Corp		100-66-3, 9011-14-7
GaAs/AlGaAs wafer	National Research Council Canada	See detailed layer structure in Figure 1.	
Ni (99.0%)	Anachemia		
Ge (99.999%)	CERAC inc.		
Au (99.999%)	Kamis inc.		
Ti (99.995%)	Kurt J Lesker		
Al	Kamis inc.		
Silver Epoxy	Epoxy Technology	H20E	